Contribution ID : 3 Type : not specified

Fully atomistic approach for ion channeling analysis of defects in Si

Monday, 26 June 2006 11:30 (1:00)

Content

Summary

 $Primary \ author(s): \quad {\rm G.\ LULLI\ (CNR,\ BOLOGNA)}$

Presenter(s): G. LULLI (CNR, BOLOGNA)

Session Classification: Fully atomistic approach for ion channeling analysis of defects in Si